

# NTST20120CT, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG, NTSB20120CTT4G



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## Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.54\text{ V}$  at  $I_F = 5\text{ A}$

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb-Free and Halide-Free Packages are Available

### Typical Applications

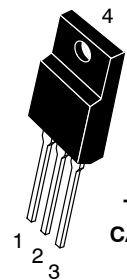
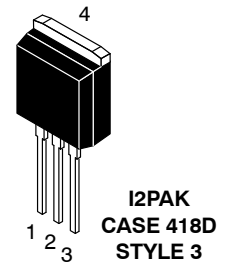
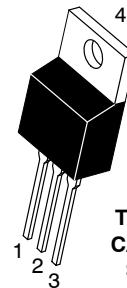
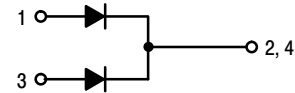
- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

### Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

VERY LOW FORWARD  
VOLTAGE, LOW LEAKAGE  
SCHOTTKY BARRIER  
RECTIFIERS 20 AMPERES,  
120 VOLTS

### PIN CONNECTIONS



### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

**NTST20120CT, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG,  
NTSB20120CTT4G**

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	120	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 130^\circ\text{C}$ )	$I_{F(AV)}$	20 10	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 135^\circ\text{C}$ )	$I_{FRM}$	40 20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	120	A
Operating Junction Temperature	$T_J$	-40 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

**THERMAL CHARACTERISTICS**

Rating	Symbol	NTST20120CTG NTSB20120CT-1G	NTSB20120CTG	NTSJ20120CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.5 70	1.43 46.8	4.42 105	$^\circ\text{C/W}$ $^\circ\text{C/W}$

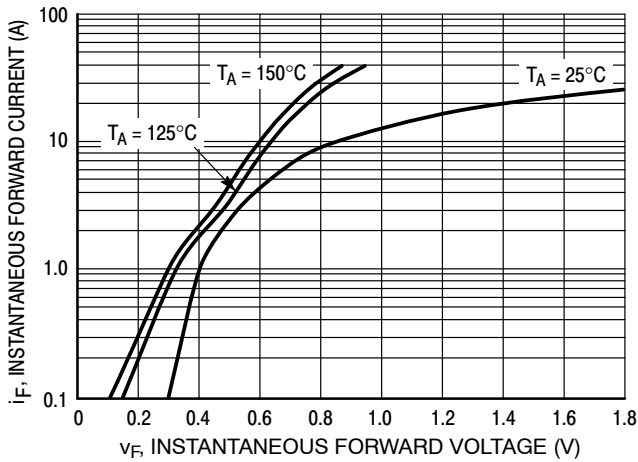
**ELECTRICAL CHARACTERISTICS** (Per Leg unless otherwise noted)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) ( $I_F = 5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 25^\circ\text{C}$ )  ( $I_F = 5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 125^\circ\text{C}$ )	$V_F$	0.62 0.90  0.54 0.64	- 1.10  - 0.72	V
Maximum Instantaneous Reverse Current (Note 1) ( $V_R = 90\text{ V}$ , $T_J = 25^\circ\text{C}$ ) ( $V_R = 90\text{ V}$ , $T_J = 125^\circ\text{C}$ )  (Rated dc Voltage, $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$I_R$	12 6  - 17	- -  700 100	$\mu\text{A}$ mA  $\mu\text{A}$ mA

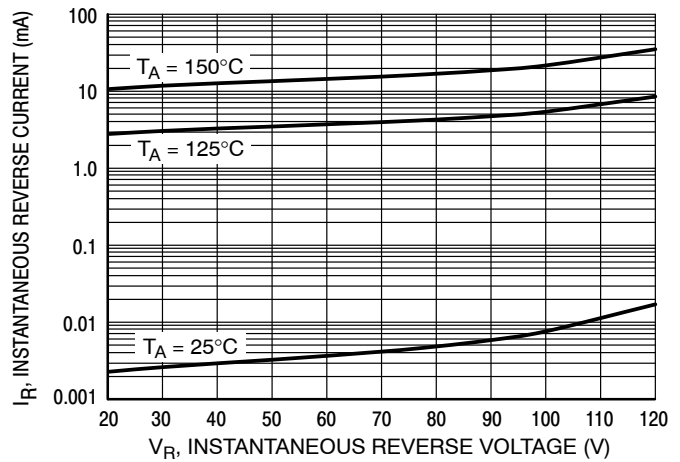
1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**NTST20120CT, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG,  
NTSB20120CTT4G**

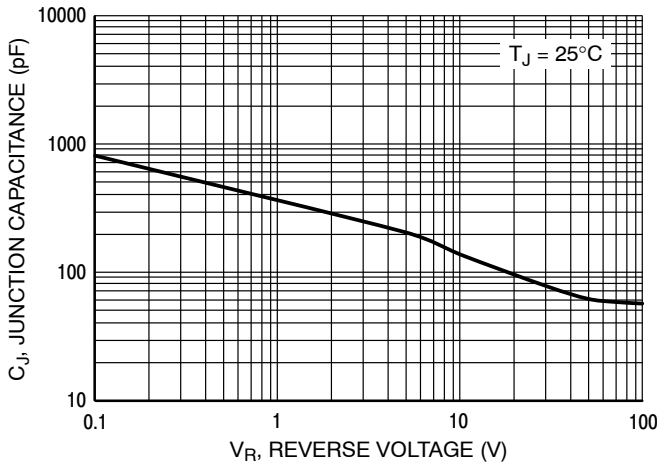
**TYPICAL CHARACTERISTICS**



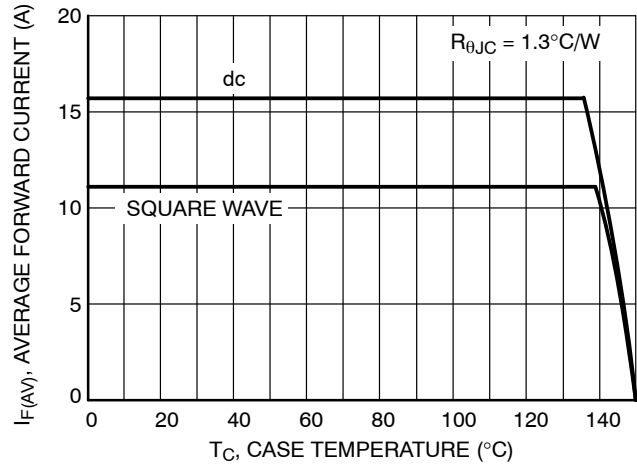
**Figure 1. Typical Instantaneous Forward Characteristics**



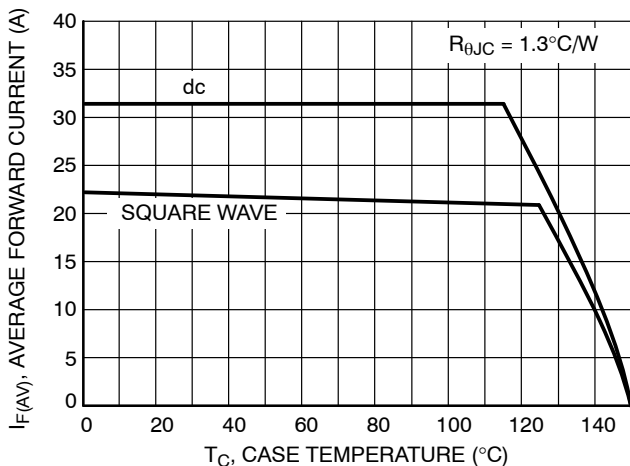
**Figure 2. Typical Reverse Current Characteristics**



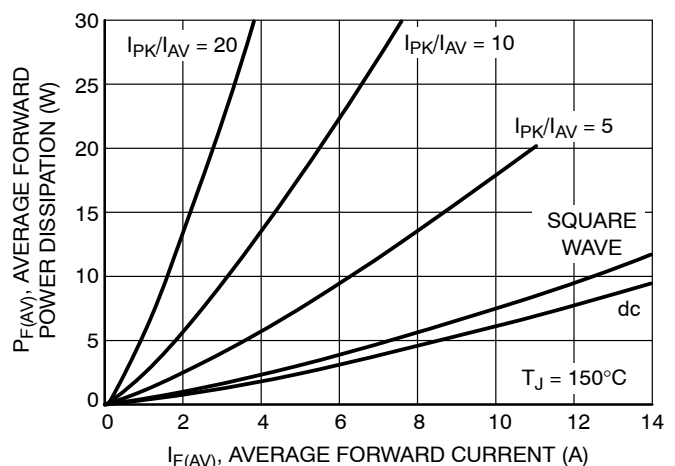
**Figure 3. Typical Junction Capacitance**



**Figure 4. Current Derating per Leg**



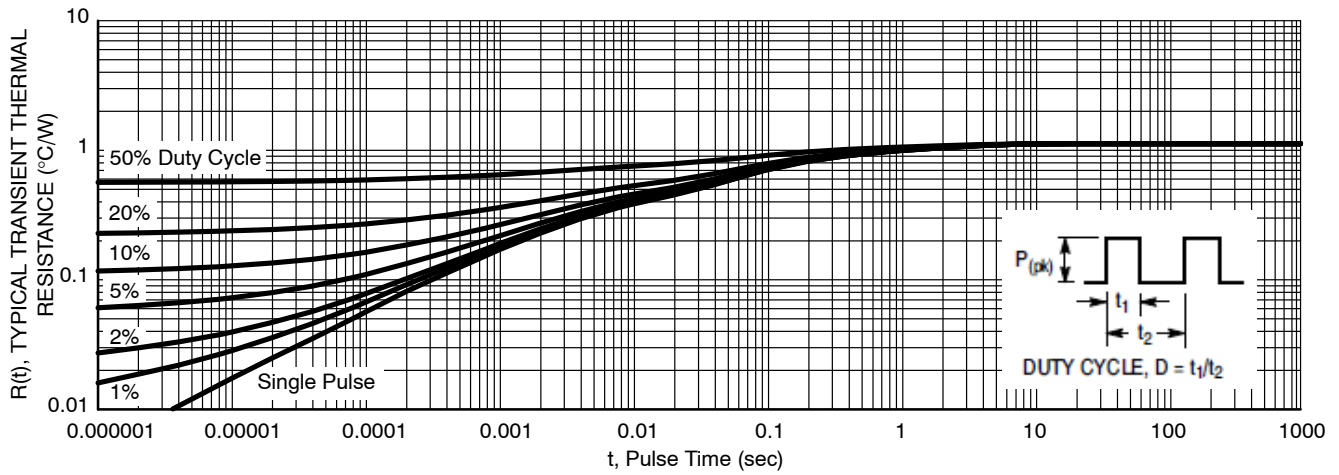
**Figure 5. Current Derating**



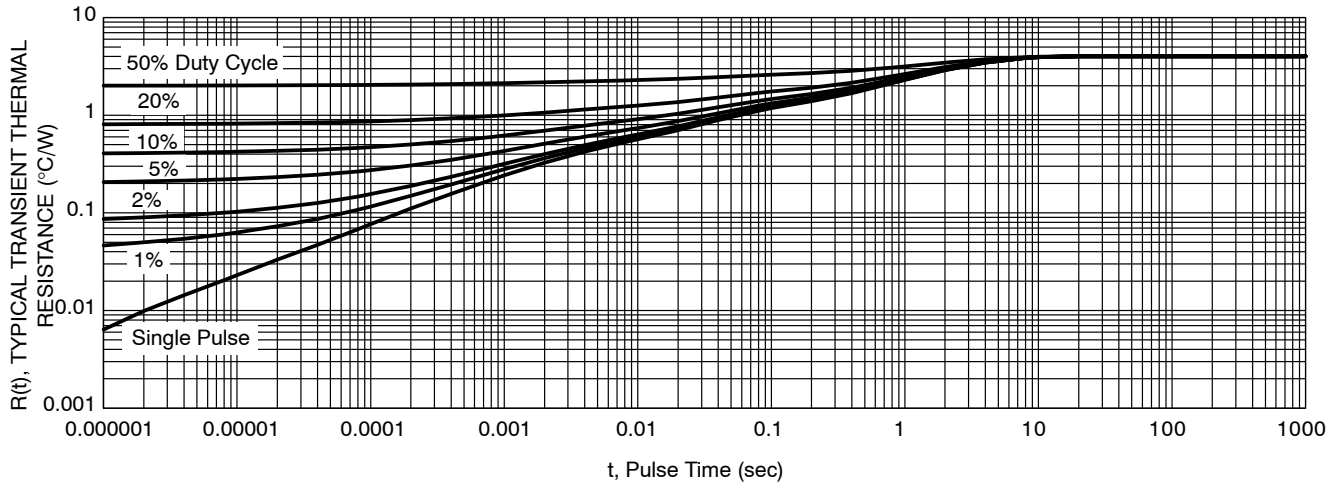
**Figure 6. Forward Power Dissipation**

**NTST20120CT, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG,  
NTSB20120CTT4G**

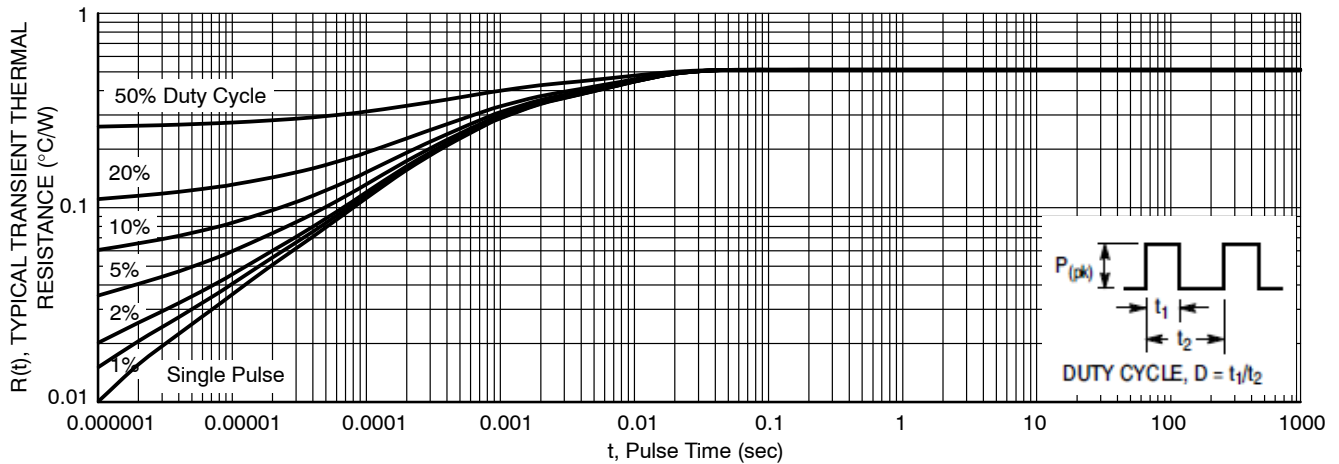
**TYPICAL CHARACTERISTICS**



**Figure 7. Typical Transient Thermal Response for NTST20120CT and NTSB20120CT-1G**



**Figure 8. Typical Transient Thermal Response for NTSJ20120CTG**



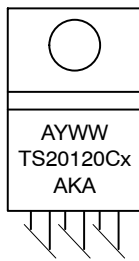
**Figure 9. Typical Transient Thermal Response for NTSB20120CTG**

**NTST20120CT, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG,  
NTSB20120CTT4G**

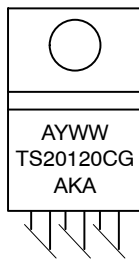
**ORDERING INFORMATION**

Device	Package	Shipping
NTST20120CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTSJ20120CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB20120CT-1G	I <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB20120CTG	D <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB20120CTT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel

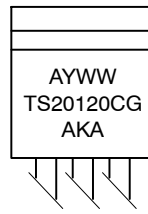
**MARKING DIAGRAMS**



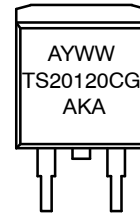
TO-220AB



TO-220FP



I<sup>2</sup>PAK



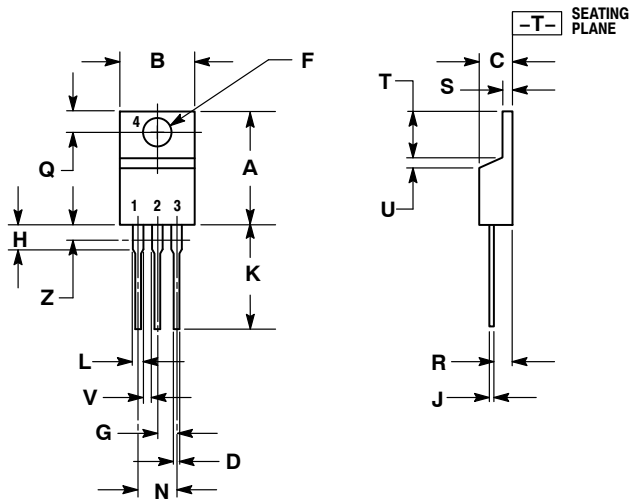
D<sup>2</sup>PAK

- A = Assembly Location
- Y = Year
- WW = Work Week
- AKA = Polarity Designator
- x = G or H
- G = Pb-Free Package
- H = Halide-Free Package

# NTST20120CT, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG, NTSB20120CTT4G

## PACKAGE DIMENSIONS

### TO-220 CASE 221A-09 ISSUE AF

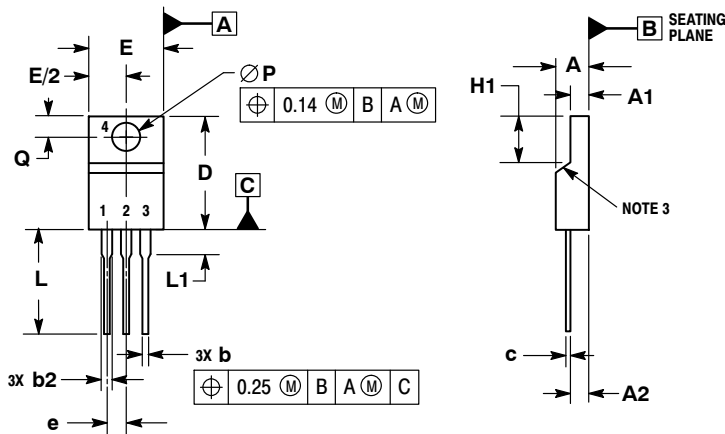


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 6:
1. ANODE
  2. CATHODE
  3. ANODE
  4. CATHODE

### TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE B



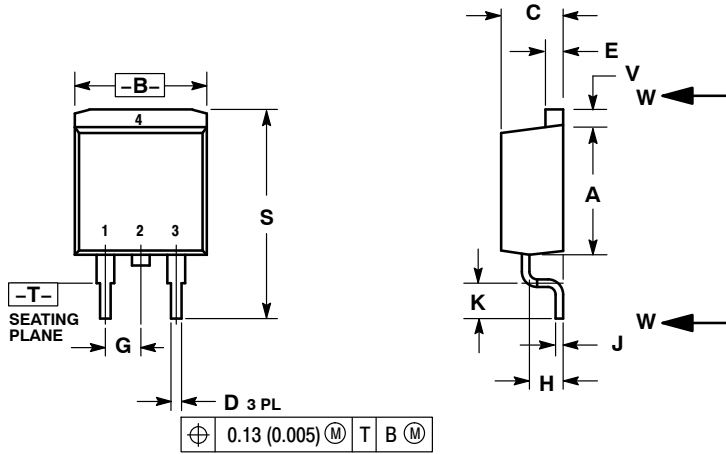
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. CONTOUR UNCONTROLLED IN THIS AREA.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
  5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

DIM	MILLIMETERS	
	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.70
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.70	7.10
L	12.70	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

**NTST20120CT, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG,  
NTSB20120CTT4G**

**PACKAGE DIMENSIONS**

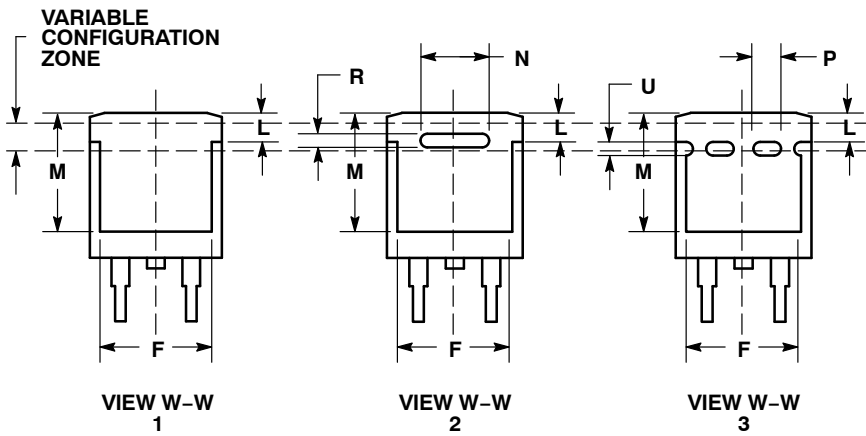
**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE K



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

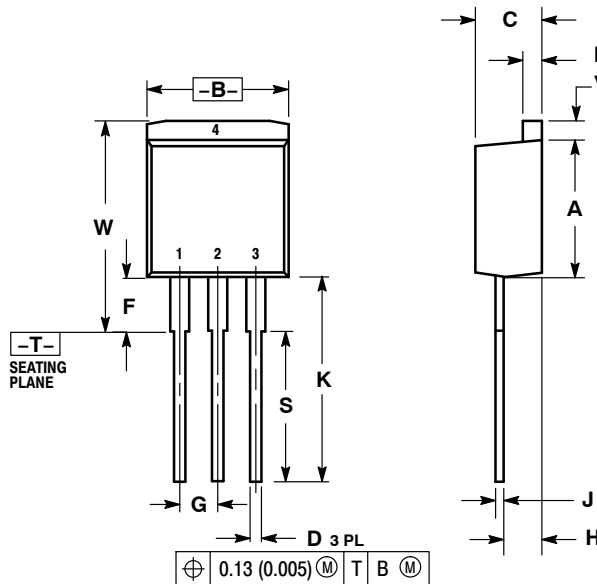
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



# NTST20120CT, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG, NTSB20120CTT4G

## PACKAGE DIMENSIONS

I<sup>2</sup>PAK (TO-262)  
CASE 418D  
ISSUE D



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.380	8.51	9.65
B	0.380	0.406	9.65	10.31
C	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
E	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
H	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

- STYLE 3:  
PIN 1: ANODE  
2: CATHODE  
3: ANODE  
4: CATHODE

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**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331